



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	Rds(ON) Max	Package	I _D T _A = +25°C
-20V	0.9Ω @ $V_{GS} = -4.5V$	SOT23	-600mA
-20 V	2.0Ω @ V _{GS} = -1.8V	30123	-420mA

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- DC-DC converters
- Power-management functions

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(TH)} < 1V</p>
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2004KQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

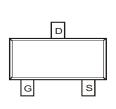
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208³
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



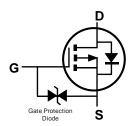


SOT23

Top View







Equivalent Circuit

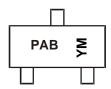
Ordering Information (Note 4)

Part Number	Dooksana	Packing		
Part Number	Package	Qty.	Carrier	
DMP2004K-7	SOT23	3,000	Tape & Reel	
DMP2004KQ-7	SOT23	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/. \\$

Marking Information



PAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: L = 2024) M = Month (ex: 9 = September)

Date Code Key

Year	2006		2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	Т		L	М	N	Р	R	S	Т	J	V	W
Month	la.	F.L	Man	A	Mari	I	11	Aug	Son	Oct	Nov	Doc
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	-20	V
Gate-Source Voltage	Vgss	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	ID	-600	mA
Pulsed Drain Current	I _{DM}	-1.9	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	Reja	227	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

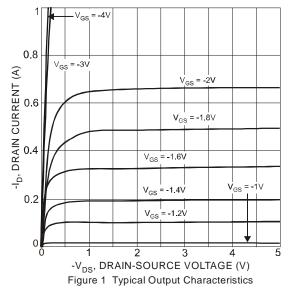
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

	1			1	1	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	-20	_	_	V	V _G S = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	1		-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		1	0.7	0.9		V _G S = -4.5V, I _D = -430mA
Static Drain-Source On-Resistance	RDS(ON)	_	1.1	1.4	Ω	Vgs = -2.5V, I _D = -300mA
		_	1.7	2.0		V _G S = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200	_	_	ms	V _{DS} = -10V, I _D = -0.2A
Diode Forward Voltage (Note 6)	VsD	-0.5	_	-1.2	V	V _G S = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	_	175	pF	
Output Capacitance	Coss	_	_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	_	20	pF	1 - 1.000112
Turn-On Delay Time	tD(ON)	_	8.5	_	ns	
Turn-On Rise Time	t _R	_	4.3	_	ns	V _{DD} = -3V, V _{GS} = -2.5V,
Turn-Off Delay Time	t _{D(OFF)}	_	20.2	_	ns	$R_L = 300\Omega, R_g = 25\Omega,$ $R_D = -100 \text{mA}$
Turn-Off Fall Time	tF	_	19.2	_	ns	- 100HIA

Notes:

- 5. Device mounted on FR-4 PCB.
- 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to product testing.





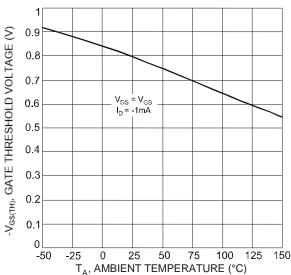


Figure 3 Gate Threshold Voltage vs. Ambient Temperature

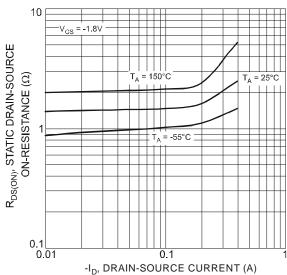
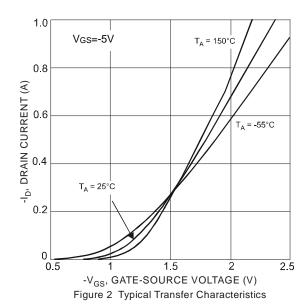


Figure 5 Static Drain-Source On-Resistance vs. Drain Current



10 V_{GS} = -4.5V NON-RESISTANCE (D) T_A = 150°C T_A = 25°C T_A = 25°C

-I_D, DRAIN-SOURCE CURRENT (A)
Figure 4 Static Drain-Source On-Resistance vs. Drain Current

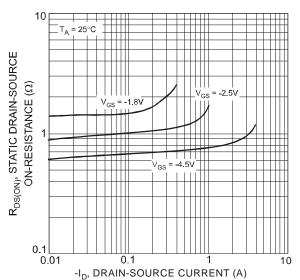


Figure 6 Static Drain-Source On-Resistance vs.
Drain-Source Current



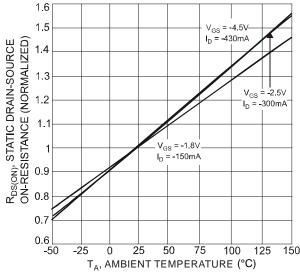


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

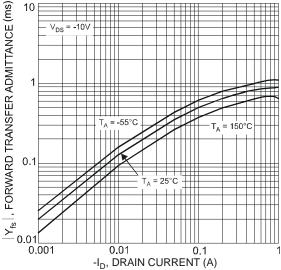
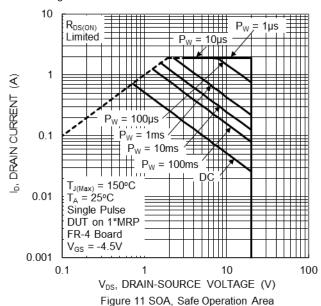


Figure 9 Forward Transfer Admittance vs. Drain Current



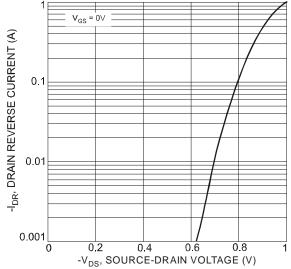
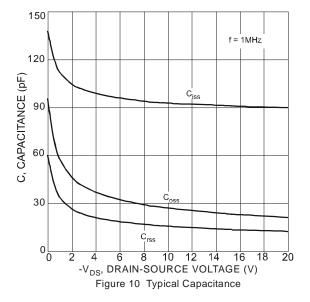


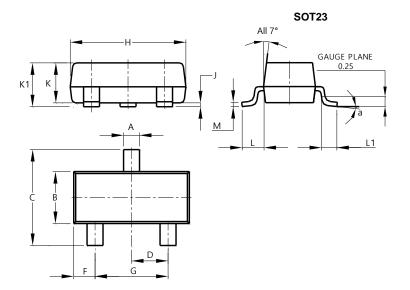
Figure 8 Reverse Drain Current vs. Source-Drain Voltage





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

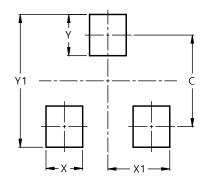


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Ξ	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K 1	0.903	1.10	1.025			
١	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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